

**Amendments to the Specification**

Please replace the paragraph on page 1 under the title "CROSS-REFERENCE TO RELATED APPLICATIONS" with the following paragraph:

This application, which is also listed below for clarity, is also a member of the following family of related U.S. Patent Application Serial Nos:

09/804,051, filed March 12, 2001 (MIO 0069 PA);  
10/796,246, filed March 9, 2004 (MIO 0069 VA); and  
11/120,941, filed May 3, 2005 (MIO 0069 V2).

This application is related to the following commonly assigned applications, but does not claim priority thereto:

09/804,421, filed March 20, 2001 (MIO 0072 PA), now U.S. Pat. No. 6,441,183;  
09/992,580, filed November 16, 2001 (MIO 0072 VA), now U.S. Pat. No. 6,884,658;  
10/229,968, filed August 28, 2002 (MIO 0072 NA), now U.S. Pat. No. 6,873,036;  
10/874,047, filed June 22, 2004 (MIO 0072 V2), now U.S. Pat. No. 7,008,823;  
10/891,772, filed July 15, 2004 (MIO 0072 V3), now U.S. Pat. No. 7,112,878;  
11/299,225, filed December 9, 2005 (MIO 0072 N2);  
09,855,731, filed May 15, 2001 (MIO 0080 PA), now U.S. Pat. No. 6,507,107;  
10/229,969, filed August 28, 2002 (MIO 0080 VA), now U.S. Pat. No. 6,869,827;  
11/013,487, filed December 16, 2004 (MIO 0080 NA); and  
11/668,127, filed January 29, 2007 (MIO 0080 V2).

Please replace the paragraph on page 15, starting on line 15 and ending on line 21 with the following paragraph:

Referring specifically to Fig. 6, a pair of decoupling capacitors 60 are mounted to the first surface 42 of the intermediate substrate 40. The thickness dimension (a) of the decoupling capacitors 60 is accommodated in a space defined by a thickness dimension (c) of the first semiconductor die 20. The pair of decoupling capacitors 60 are mounted to the first surface 42 of the intermediate substrate 40. The first semiconductor die 20 is positioned between the pair of decoupling capacitors 60 relative to the first surface 42 of the intermediate substrate 40.